



SSC8L64GN6

N-Channel Enhanced MOSFET

➤ Features

VDS	VGS	RDSON Typ.	ID
60V	±20V	4.4mΩ@10V	90A
		6.3mΩ@4V5	

➤ Description

This device is N-Channel enhancement MOSFET. Uses SGT technology and design to provide excellent RDSON with low gate charge. This device is suitable for use in DC-DC conversion, power switch and charging circuit.

100% UIS + ΔVds + Rg Tested!

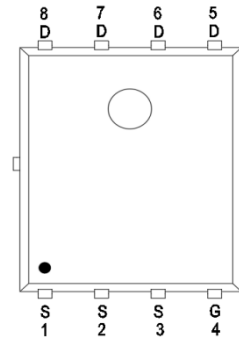
➤ Applications

- DC/DC converters
- Power supplies
- Motor Drive Control
- Synchronous rectification

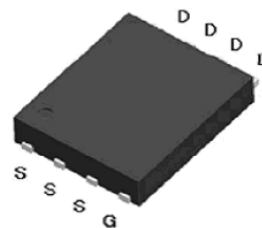
➤ Ordering Information

Device	Package	Shipping
SSC8L64GN6	PDFN5X6-8L	5000/Reel

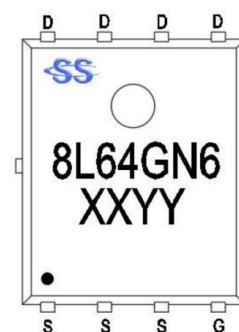
➤ Pin configuration



Top View



PDFN5X6-8L



Marking

(XX: product year / YY: product week)



➤ **Absolute Maximum Ratings**($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Unit	
V_{DSS}	Drain-to-Source Voltage	60	V	
V_{GSS}	Gate-to-Source Voltage	± 20	V	
I_D	Continuous Drain Current ^d	$T_C=25^{\circ}\text{C}$	90	A
		$T_C=100^{\circ}\text{C}$	47	
I_{DSM}	Continuous Drain Current ^a	$T_A=25^{\circ}\text{C}$	27	A
		$T_A=70^{\circ}\text{C}$	19	
I_{DM}	Pulsed Drain Current ^b	350	A	
P_D	Power Dissipation ^c	$T_C=25^{\circ}\text{C}$	56	W
		$T_C=100^{\circ}\text{C}$	22	
P_{DSM}	Power Dissipation ^a	$T_A=25^{\circ}\text{C}$	5.2	W
		$T_A=70^{\circ}\text{C}$	3.3	
I_{AS}	Avalanche Current ^b L=0.5mH Single Pulse	22	A	
E_{AS}	Avalanche Energy ^b L=0.5mH Single Pulse	121	mJ	
T_J	Operation junction temperature	-55~150	$^{\circ}\text{C}$	
T_{STG}	Storage temperature range	-55~150		

➤ **Thermal Resistance Ratings**($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Unit
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance ^a	24	$^{\circ}\text{C}/\text{W}$
$R_{\theta JC}$	Junction-to-Case Thermal Resistance	2.2	

Note:

- The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz.copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The value in any given application depends on the user is specific board design. The power dissipation is based on the $t \leq 10\text{s}$ thermal resistance rating.
- Repetitive rating, pulse width limited by junction temperature.
- The power dissipation P_D is based on $T_{J(\text{MAX})}=150^{\circ}\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.
- The maximum current rating is package limited.

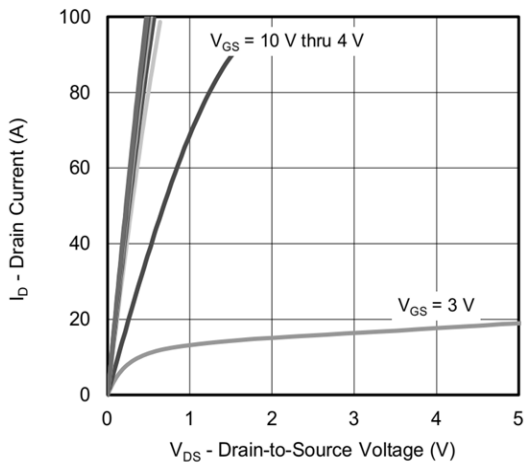


➤ **Electronics Characteristics**($T_A=25^{\circ}\text{C}$ unless otherwise noted)

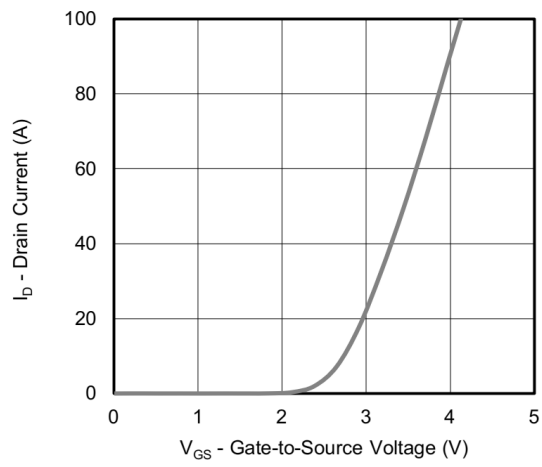
Symbol	Parameter	Test Conditions	Min	Typ.	Max	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.9	2.4	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V, I_D=40A$		4.4	5.2	mΩ
		$V_{GS}=4.5V, I_D=20A$		6.3	7.5	
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=60V, V_{GS}=0V$			1	μA
I_{GSS}	Gate-Source leak current	$V_{GS}=\pm 20V, V_{DS}=0V$			±100	nA
G_{FS}	Transconductance	$V_{DS}=5V, I_D=20A$		38		S
V_{SD}	Forward Voltage	$V_{GS}=0V, I_S=20A$		0.83	1.3	V
R_g	Gate Resistance	$V_{DS}=0V, f=1\text{MHz}$		0.8		Ω
C_{iss}	Input Capacitance	$V_{DS}=30V, V_{GS}=0V, f=1\text{MHz}$		2100		pF
C_{oss}	Output Capacitance			850		
C_{rss}	Reverse Transfer Capacitance			46		
$T_{D(ON)}$	Turn-on delay time	$V_{GS}=10V, R_L=1.5\Omega$ $V_{DS}=30V, R_G=3\Omega$		8		ns
T_r	Rise time			6		
$T_{D(OFF)}$	Turn-off delay time			42		
T_f	Fall time			12		
Q_G	Total Gate Charge	$V_{GS}=10V, V_{DS}=30V$ $I_D=20A$		38		nC
Q_{GS}	Gate Source Charge			4.4		
Q_{GD}	Gate Drain Charge			10.6		
T_{rr}	Diode Recovery Time	$I_F=20A, di/dt=500A/\mu s$		18		ns
Q_{rr}	Diode Recovery Charge	$I_F=20A, di/dt=500A/\mu s$		76		nC



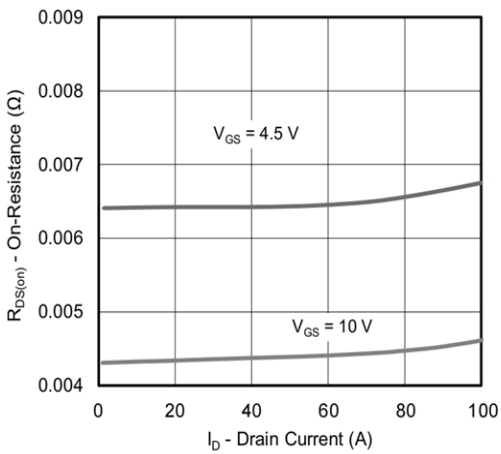
➤ **Typical Characteristics** ($T_A=25^\circ\text{C}$ unless otherwise noted)



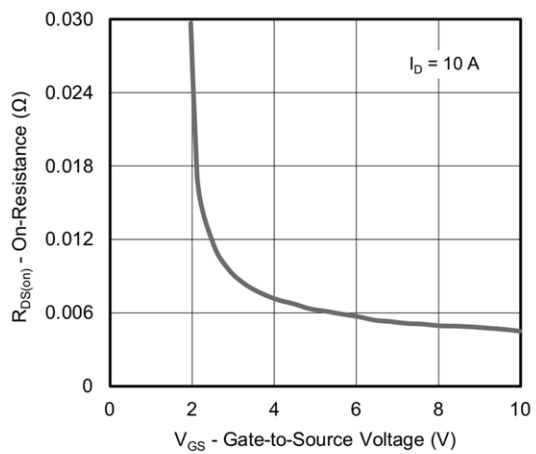
Output Characteristics



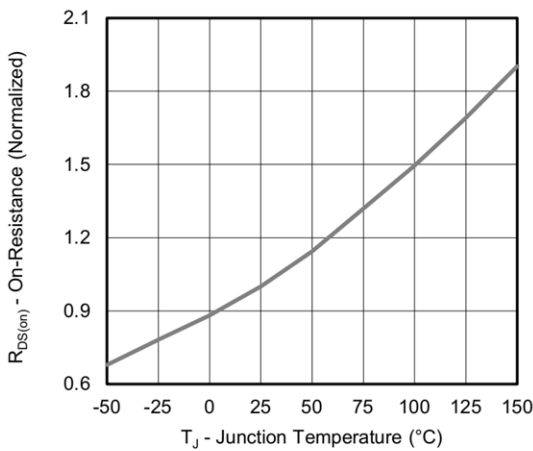
Transfer Characteristics



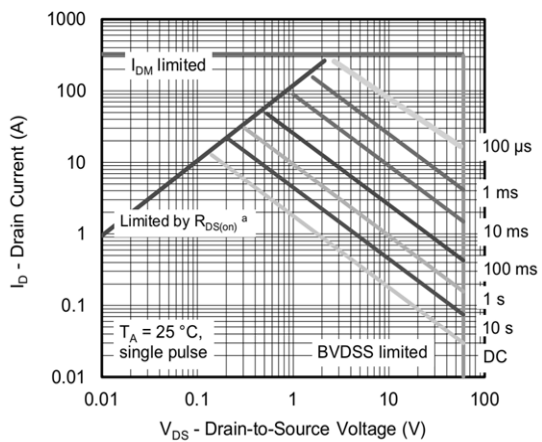
On-Resistance vs. Drain Current and Gate Voltage



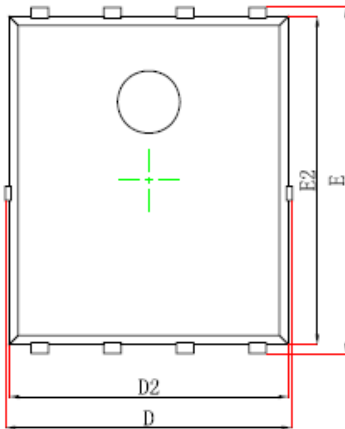
On-Resistance vs. Gate-to-Source Voltage



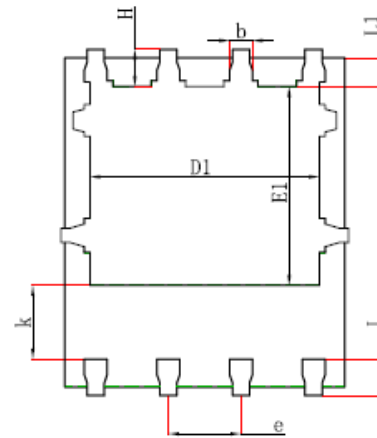
On-Resistance vs. Junction Temperature



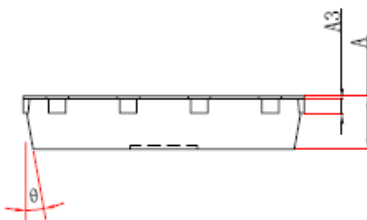
Safe Operating Area, Junction-to-Ambient

➤ Package Information


Top View
[顶视图]



Bottom View
[背视图]



Side View
[侧视图]

Package: PDNF5X6-8L

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF		0.010REF	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP		0.050TYP	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°



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